

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Seong-Ju PARK et al.

Application No.: New U.S. Application

Filed: November 6, 2003

Docket No.: 117683

For: METHOD FOR MANUFACTURING ZINC OXIDE SEMICONDUCTORS

INFORMATION DISCLOSURE STATEMENT

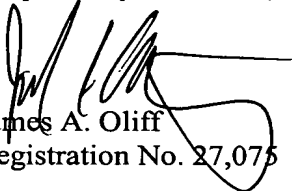
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 CFR §1.56, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO-1449. Unless otherwise indicated herein, one copy of each reference is attached. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

- ☒ 1. This Information Disclosure Statement is being filed (a) within three months of the U.S. filing date of this non-CPA application, OR (b) before the mailing date of a first Office Action on the merits in the present application. No certification or fee is required.
- ☒ 2. Relevance of the references 1-5 is discussed in the present specification.

Respectfully submitted,


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Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 117683		APPLICATION NO. New U.S. Application	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANT(S) Seong-Ju PARK et al.			
				FILING DATE November 6, 2003		GROUP	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
	1.	"Tetsuya Yamamoto et al.; "Solution Using a Codoping Method to Unipolarity for the Fabrication of p-Type ZnO"; Jpn. J. Appl. Phys.; Vol. 38, Part 2, No. 2B; February 15 1999; pp L166-L169					
	2.	Mathew Joseph et al.; "p-Type Electrical Conduction in ZnO Thin Films by Ga and N Codoping"; Jpn. J. Appl. Phys.; Vol. 38, Part 2, No. 11A; November 1, 1999; pp L1205-L1207					
	3.	Toru Aoki et al.; "ZnO diode fabricated by excimer-laser doping"; Applied Physics Letters; Vol. 76, No. 22; May 29, 2000; pp 3257-3258					
	4.	Y. R. Ryu et al.; "Synthesis of p-type ZnO films"; Journal of Crystal Growth; 2000; pp 330-334					
	5.	D.C. Look et al.; "Characterization of homoepitaxial p-type ZnO grown by molecular beam epitaxy"; Applied Physics Letters; Vol 81, No. 10; September 2, 2002; pp 1830-1832					
EXAMINER					DATE CONSIDERED		
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Date: November 6, 2003